



STW8NA60 STH8NA60FI

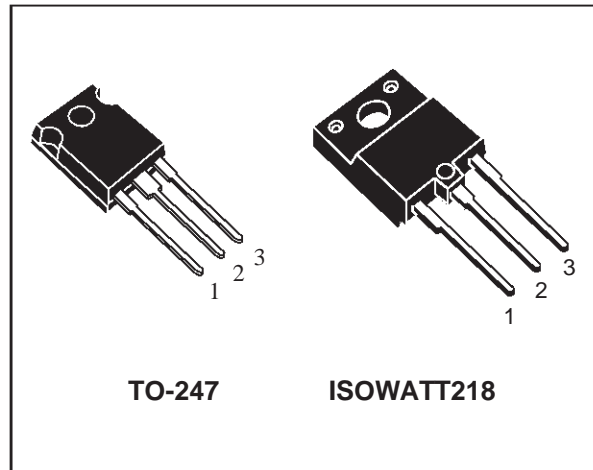
N - CHANNEL ENHANCEMENT MODE FAST POWER MOS TRANSISTOR

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|------------|------------------|---------------------|----------------|
| STW8NA60 | 600 V | < 1 Ω | 8 A |
| STH8NA60FI | 600 V | < 1 Ω | 5 A |

- TYPICAL R_{DS(on)} = 0.92 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | | Unit |
|---------------------|---|------------|------------|------|
| | | STW8NA60 | STH8NA60FI | |
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 600 | | V |
| V _{DGR} | Drain- gate Voltage (R _{GS} = 20 kΩ) | 600 | | V |
| V _{GS} | Gate-source Voltage | ± 30 | | V |
| I _D | Drain Current (continuous) at T _c = 25 °C | 8 | 5 | A |
| I _D | Drain Current (continuous) at T _c = 100 °C | 5.1 | 3.2 | A |
| I _{DM} (•) | Drain Current (pulsed) | 32 | 32 | A |
| P _{tot} | Total Dissipation at T _c = 25 °C | 150 | 60 | W |
| | Derating Factor | 1.2 | 0.48 | W/°C |
| V _{ISO} | Insulation Withstand Voltage (DC) | — | 4000 | V |
| T _{stg} | Storage Temperature | -65 to 150 | | °C |
| T _j | Max. Operating Junction Temperature | 150 | | °C |

(•) Pulse width limited by safe operating area

STW8NA60-STH8NA60FI

THERMAL DATA

| | | | TO-247 | ISOWATT218 | |
|-----------------------|--|-----|--------|------------|------|
| R _{thj-case} | Thermal Resistance Junction-case | Max | 0.83 | 2.08 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-ambient | Max | 30 | | °C/W |
| R _{thc-sink} | Thermal Resistance Case-sink | Typ | 0.1 | | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | | 300 | | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%) | 8 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 480 | mJ |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|--|------|------|-----------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA V _{GS} = 0 | 600 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating T _c = 100 °C | | | 25 250 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 30 V | | | ± 100 | nA |

ON (*)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|---|------|------|------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} I _D = 250 μA | 2.25 | 3 | 3.75 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V I _D = 4 A | | 0.92 | 1 | Ω |
| I _{D(on)} | On State Drain Current | V _{DS} > I _{D(on)} × R _{DS(on)max} V _{GS} = 10 V | 8 | | | A |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g _{fs} (*) | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)max} I _D = 4 A | 4.5 | 6.6 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25 V f = 1 MHz V _{GS} = 0 | | 1350 | 1690 | pF |
| C _{oss} | Output Capacitance | | | 175 | 230 | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 45 | 60 | pF |

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------|-----------------------|--|------|------|------|------------------|
| $t_{d(on)}$ | Turn-on Time | $V_{DD} = 300\text{ V}$ $I_D = 4\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3) | | 20 | 28 | ns |
| t_r | Rise Time | | | 35 | 35 | ns |
| $(di/dt)_{on}$ | Turn-on Current Slope | $V_{DD} = 480\text{ V}$ $I_D = 8\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5) | | 200 | | A/ μs |
| Q_g | Total Gate Charge | $V_{DD} = 480\text{ V}$ $I_D = 8\text{ A}$ $V_{GS} = 10\text{ V}$ | | 58 | 82 | nC |
| Q_{gs} | Gate-Source Charge | | | 9 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 27 | | nC |

SWITCHING OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-----------------------|--|------|------|------|------|
| $t_{r(off)}$ | Off-voltage Rise Time | $V_{DD} = 640\text{ V}$ $I_D = 8\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5) | | 16 | 23 | ns |
| t_f | Fall Time | | | 16 | 23 | ns |
| t_c | Cross-over Time | | | 26 | 37 | ns |

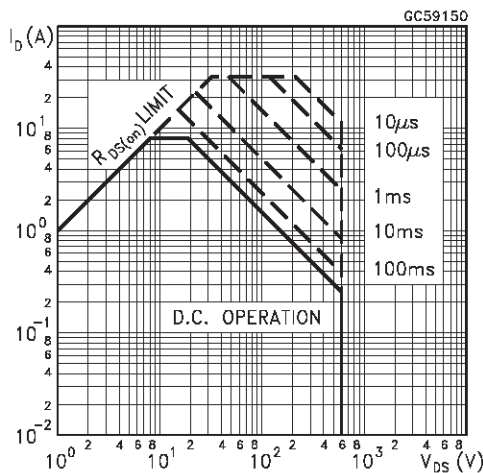
SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------------|-------------------------------|---|------|------|------|---------------|
| I_{SD} | Source-drain Current | | | | 8 | A |
| $I_{SDM}(\bullet)$ | Source-drain Current (pulsed) | | | | 32 | A |
| $V_{SD}(\ast)$ | Forward On Voltage | $I_{SD} = 8\text{ A}$ $V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 8\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5) | | 600 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 10 | | μC |
| I_{RRM} | Reverse Recovery Current | | | 33 | | A |

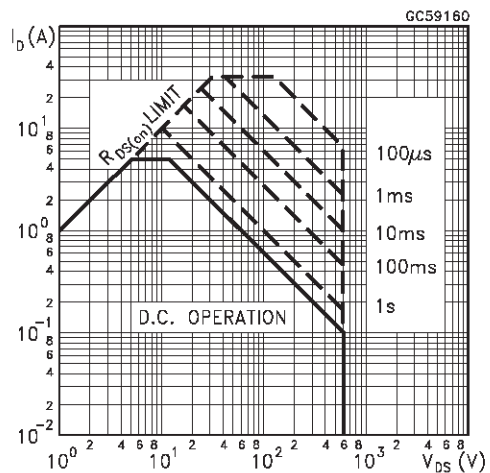
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

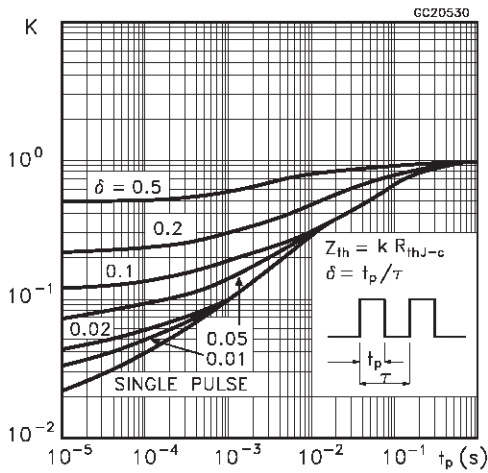
Safe Operating Area for TO-247



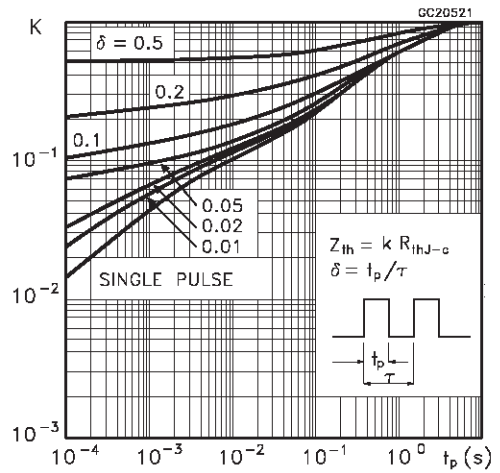
Safe Operating Area for ISOWATT218



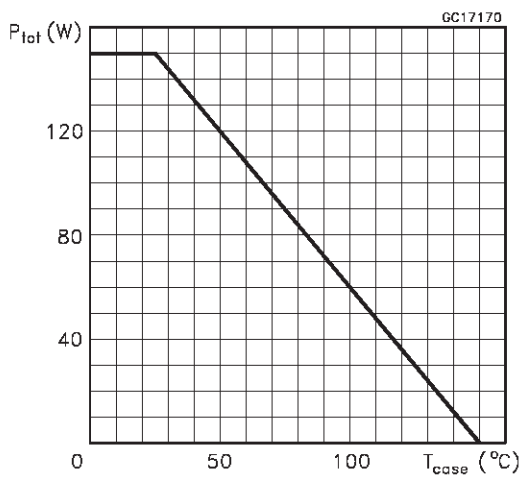
Thermal Impedance for TO-247



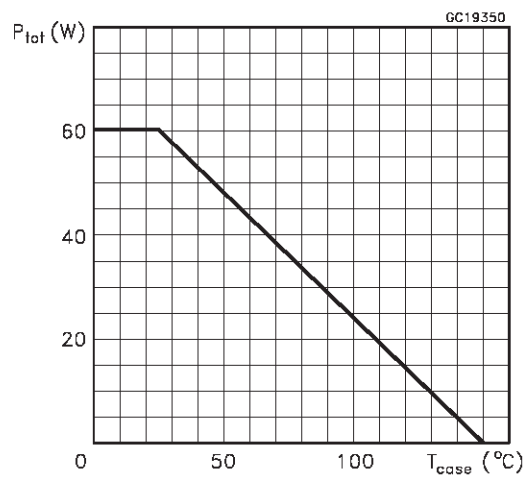
Thermal Impedance for ISOWATT218



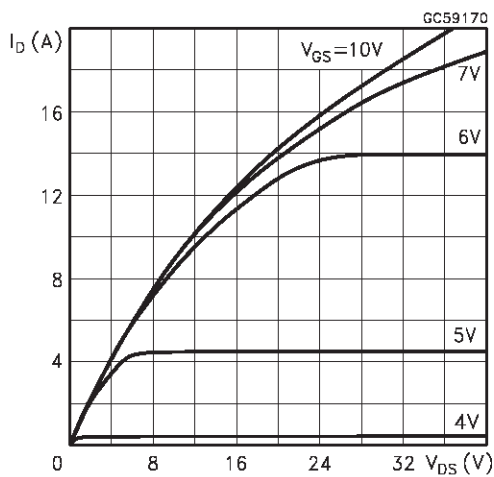
Derating Curve for TO-247



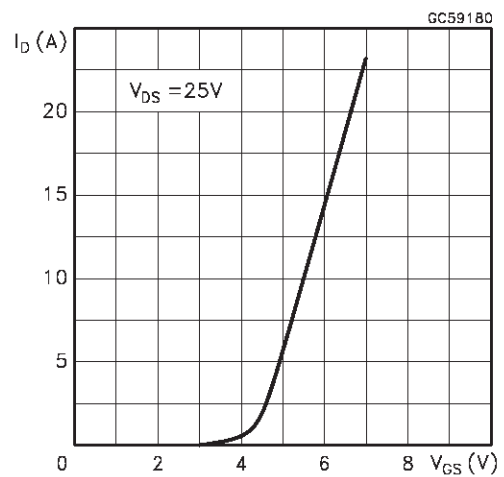
Derating Curve for ISOWATT218



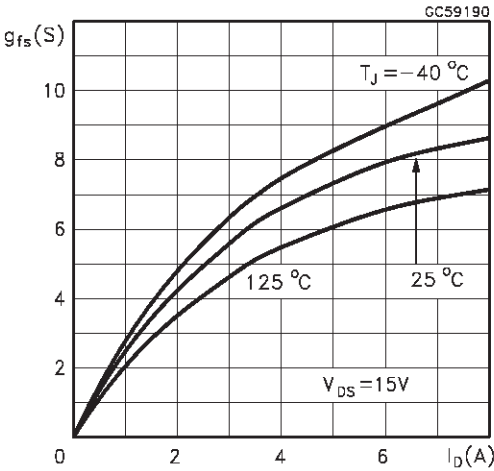
Output Characteristics



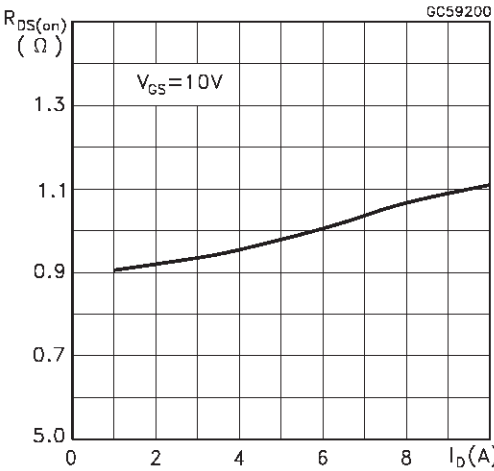
Transfer Characteristics



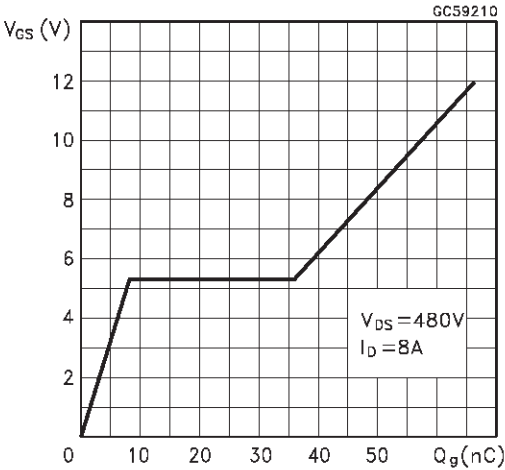
Transconductance



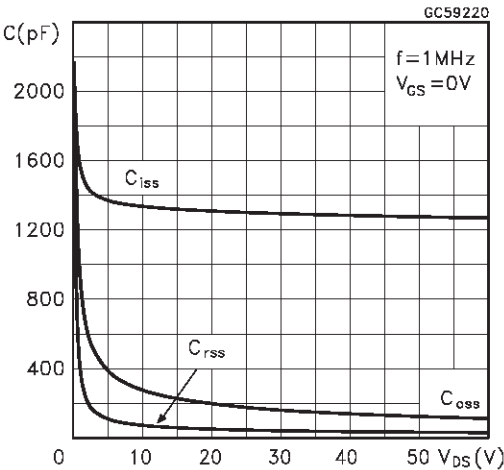
Static Drain-source On Resistance



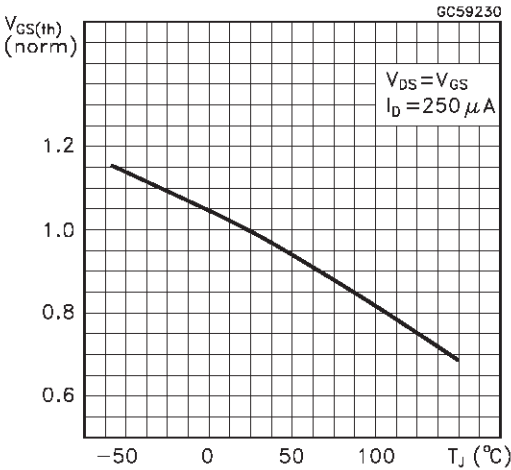
Gate Charge vs Gate-source Voltage



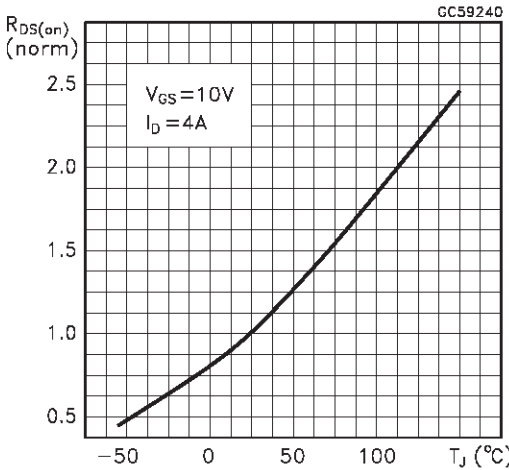
Capacitance Variations



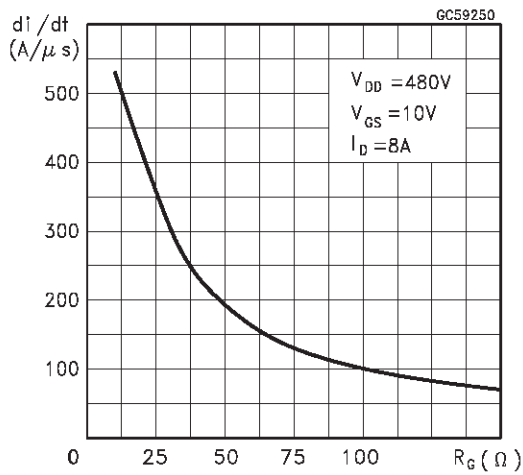
Normalized Gate Threshold Voltage vs Temperature



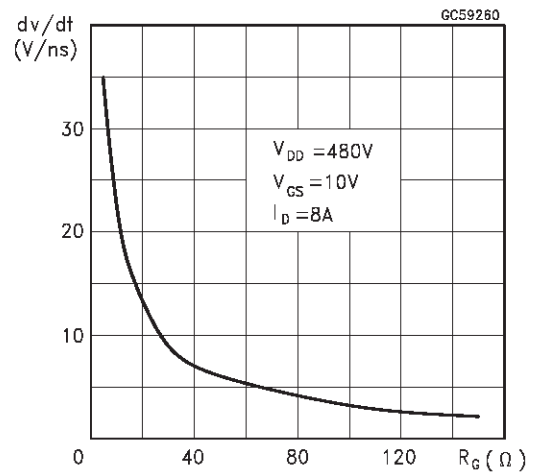
Normalized On Resistance vs Temperature



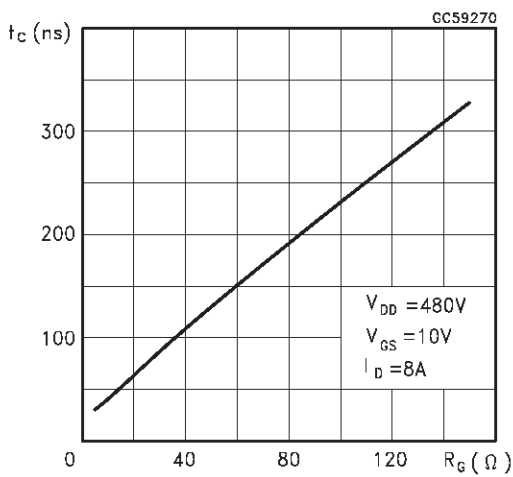
Turn-on Current Slope



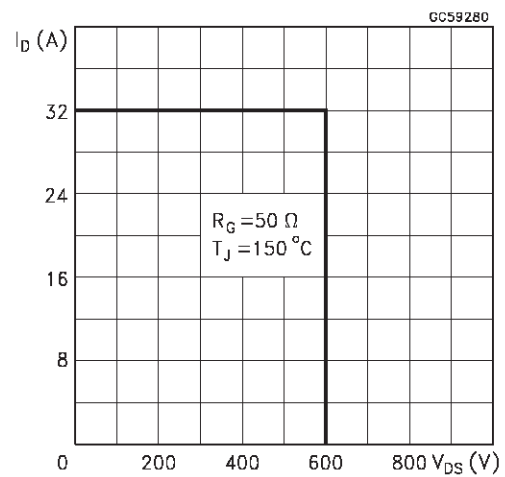
Turn-off Drain-source Voltage Slope



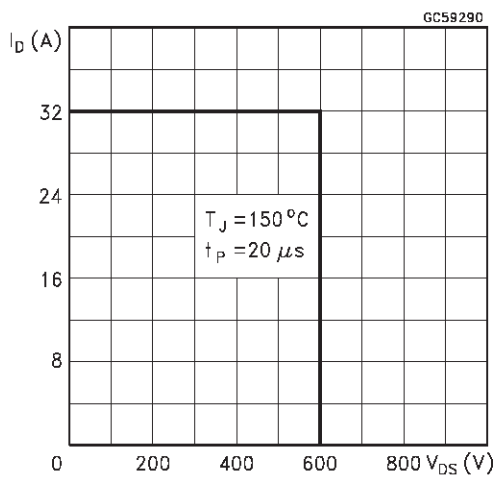
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

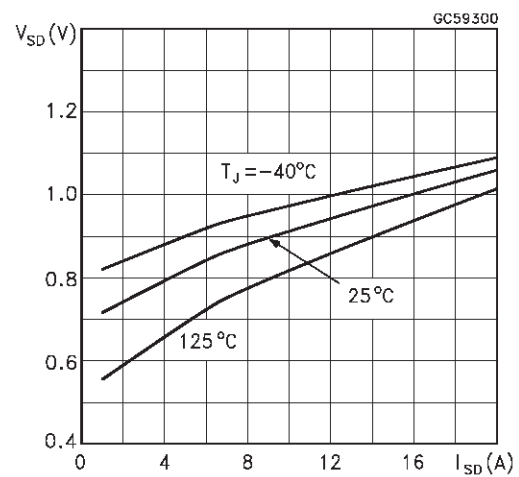


Fig. 1: Unclamped Inductive Load Test Circuit

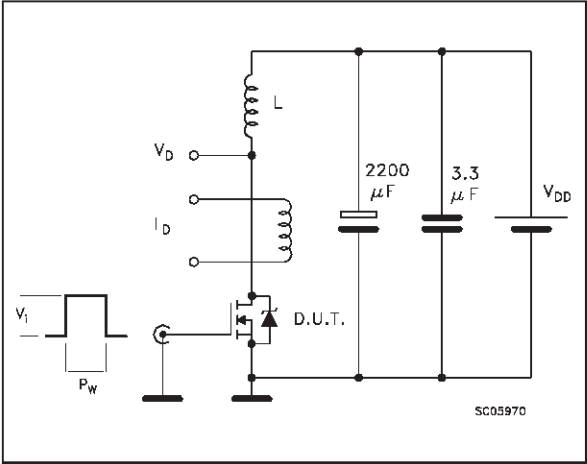


Fig. 2: Unclamped Inductive Waveform

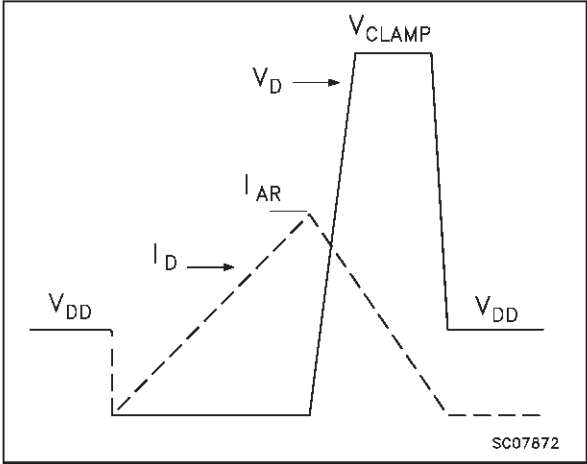


Fig. 3: Switching Times Test Circuits For Resistive Load

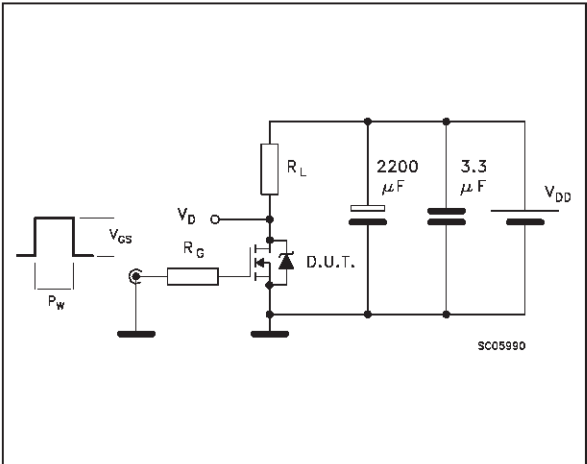


Fig. 4: Gate Charge test Circuit

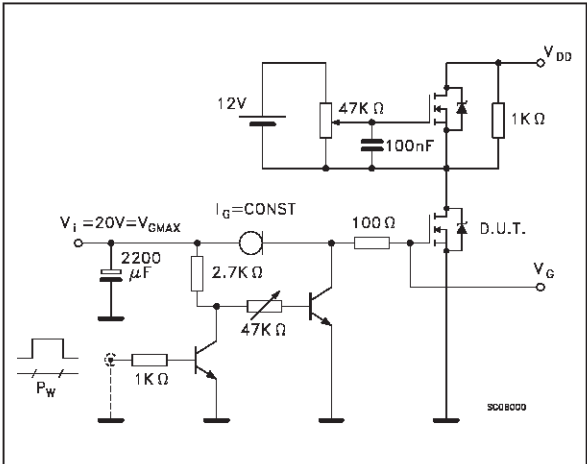
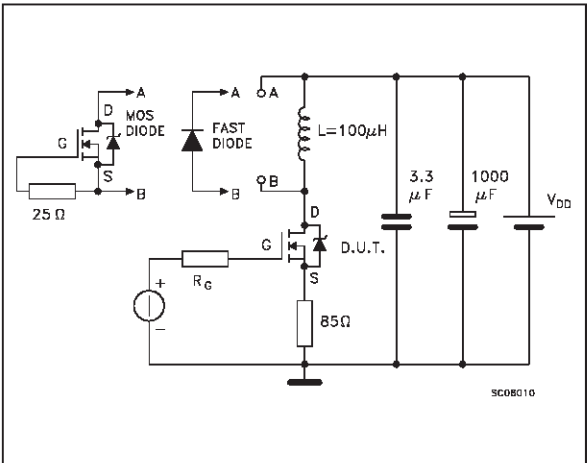
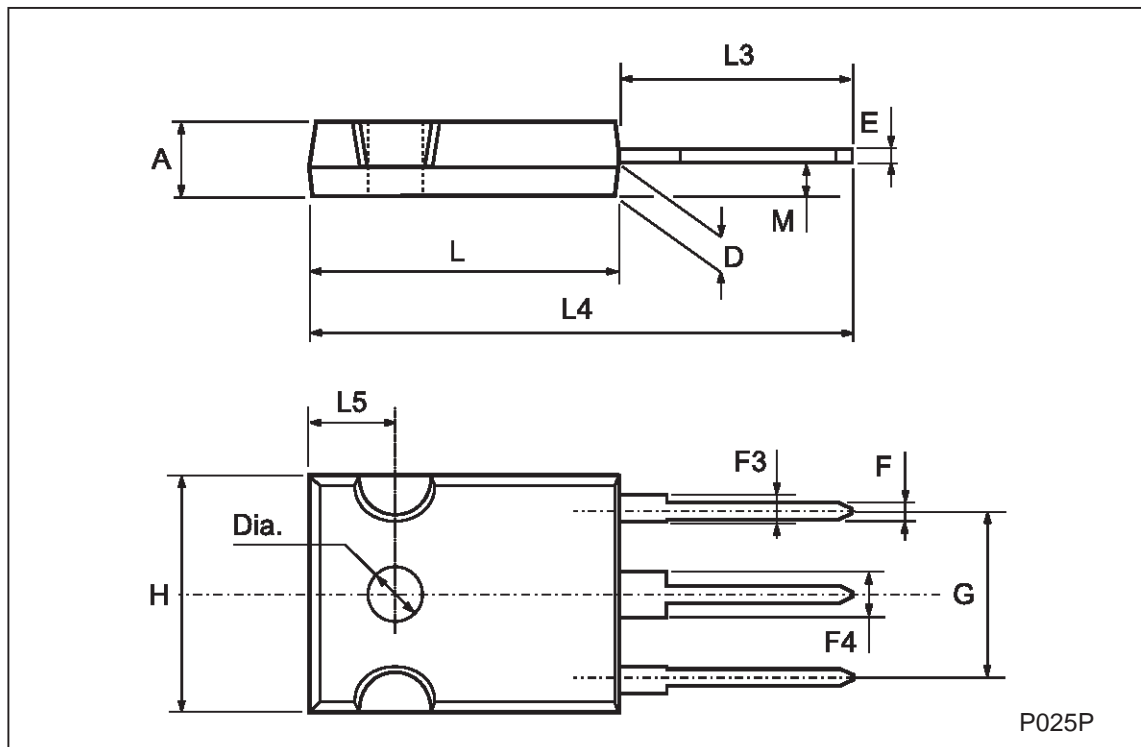


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

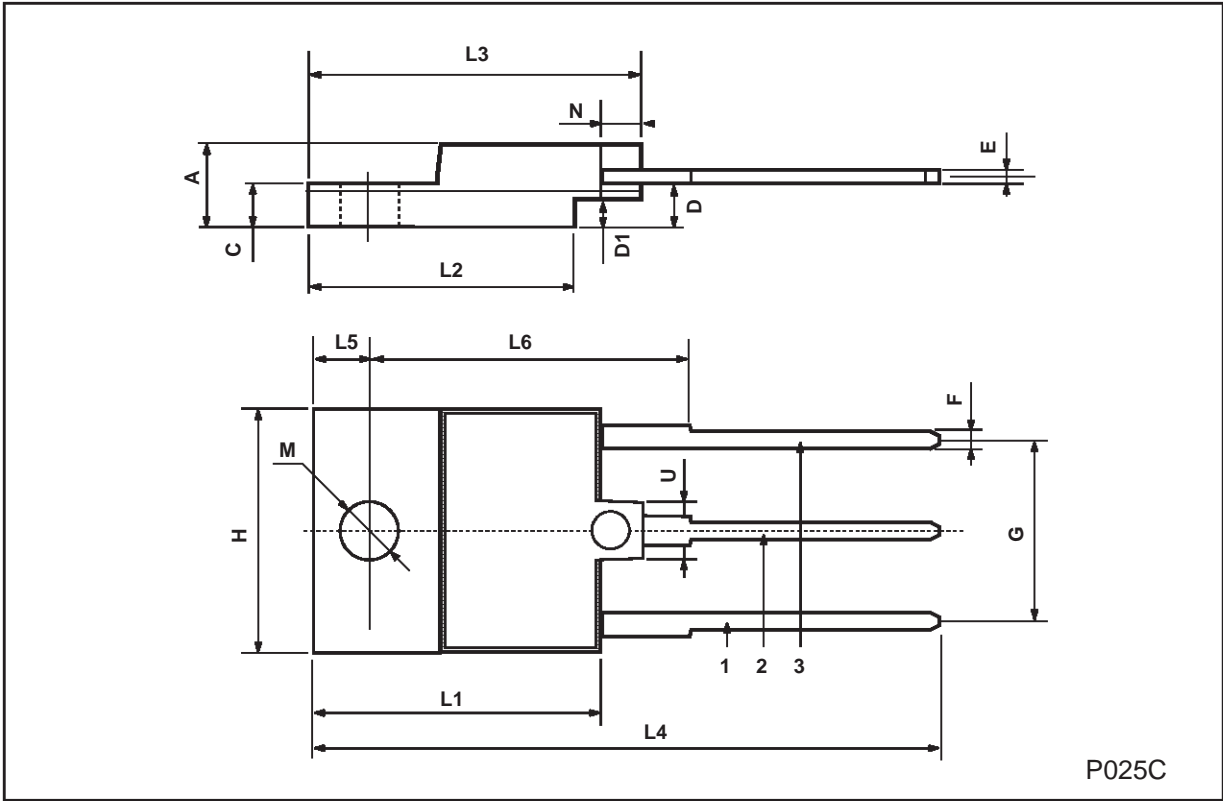
| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.7 | | 5.3 | 0.185 | | 0.209 |
| D | 2.2 | | 2.6 | 0.087 | | 0.102 |
| E | 0.4 | | 0.8 | 0.016 | | 0.031 |
| F | 1 | | 1.4 | 0.039 | | 0.055 |
| F3 | 2 | | 2.4 | 0.079 | | 0.094 |
| F4 | 3 | | 3.4 | 0.118 | | 0.134 |
| G | | 10.9 | | | 0.429 | |
| H | 15.3 | | 15.9 | 0.602 | | 0.626 |
| L | 19.7 | | 20.3 | 0.776 | | 0.779 |
| L3 | 14.2 | | 14.8 | 0.559 | 0.413 | 0.582 |
| L4 | | 34.6 | | | 1.362 | |
| L5 | | 5.5 | | | 0.217 | |
| M | 2 | | 3 | 0.079 | | 0.118 |
| Dia | 3.55 | | 3.65 | 0.140 | | 0.144 |



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ISOWATT218 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 5.35 | | 5.65 | 0.210 | | 0.222 |
| C | 3.3 | | 3.8 | 0.130 | | 0.149 |
| D | 2.9 | | 3.1 | 0.114 | | 0.122 |
| D1 | 1.88 | | 2.08 | 0.074 | | 0.081 |
| E | 0.75 | | 1 | 0.029 | | 0.039 |
| F | 1.05 | | 1.25 | 0.041 | | 0.049 |
| G | 10.8 | | 11.2 | 0.425 | | 0.441 |
| H | 15.8 | | 16.2 | 0.622 | | 0.637 |
| L1 | 20.8 | | 21.2 | 0.818 | | 0.834 |
| L2 | 19.1 | | 19.9 | 0.752 | | 0.783 |
| L3 | 22.8 | | 23.6 | 0.897 | | 0.929 |
| L4 | 40.5 | | 42.5 | 1.594 | | 1.673 |
| L5 | 4.85 | | 5.25 | 0.190 | | 0.206 |
| L6 | 20.25 | | 20.75 | 0.797 | | 0.817 |
| M | 3.5 | | 3.7 | 0.137 | | 0.145 |
| N | 2.1 | | 2.3 | 0.082 | | 0.090 |
| U | | 4.6 | | | 0.181 | |



P025C

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